

# Zhenyu Yang

## List of Publications by Year in descending order

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19  
papers

1,128  
citations

759233

12  
h-index

794594

19  
g-index

19  
all docs

19  
docs citations

19  
times ranked

2201  
citing authors

#	ARTICLE	IF	CITATIONS
1	Metal Ion-Modified Black Phosphorus with Enhanced Stability and Transistor Performance. <i>Advanced Materials</i> , 2017, 29, 1703811.	21.0	431
2	Enhanced Photoresponsivity of a GaAs Nanowire Metal-Semiconductor-Metal Photodetector by Adjusting the Fermi Level. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 33188-33193.	8.0	151
3	MoS <sub>2</sub> Negative Capacitance Field-Effect Transistors with Subthreshold Swing below the Physics Limit. <i>Advanced Materials</i> , 2018, 30, e1800932.	21.0	87
4	Enhancing Photoresponsivity of Self-Aligned MoS <sub>2</sub> Field-Effect Transistors by Piezo-Phototronic Effect from GaN Nanowires. <i>ACS Nano</i> , 2016, 10, 7451-7457.	14.6	86
5	WSe <sub>2</sub> /GeSe heterojunction photodiode with giant gate tunability. <i>Nano Energy</i> , 2018, 49, 103-108.	16.0	73
6	Controlled synthesis of high-quality crystals of monolayer MoS <sub>2</sub> for nanoelectronic device application. <i>Science China Materials</i> , 2016, 59, 182-190.	6.3	51
7	High-Performance Photoinduced Memory with Ultrafast Charge Transfer Based on MoS <sub>2</sub> /SWCNTs Network Van Der Waals Heterostructure. <i>Small</i> , 2019, 15, e1804661.	10.0	42
8	Performance Limits of the Self-Aligned Nanowire Top-Gated MoS <sub>2</sub> Transistors. <i>Advanced Functional Materials</i> , 2017, 27, 1602250.	14.9	37
9	Interface engineering for two-dimensional semiconductor transistors. <i>Nano Today</i> , 2019, 25, 122-134.	11.9	35
10	The photovoltaic and photoconductive photodetector based on GeSe/2D semiconductor van der Waals heterostructure. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	30
11	Advanced tape-exfoliated method for preparing large-area 2D monolayers: a review. <i>2D Materials</i> , 2021, 8, 032002.	4.4	30
12	Black Phosphorus Infrared Photodetectors with Fast Response and High Photoresponsivity. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018, 12, 1800310.	2.4	28
13	High-current MoS <sub>2</sub> transistors with non-planar gate configuration. <i>Science Bulletin</i> , 2021, 66, 777-782.	9.0	12
14	On-Chip Detection of Multiwavelength Surface Plasmon Polaritons Based on Plasmonic Demultiplexers. <i>ACS Photonics</i> , 2022, 9, 391-397.	6.6	12
15	InGaZnO Tunnel and Junction Transistors Based on Vertically Stacked Black Phosphorus/InGaZnO Heterojunctions. <i>Advanced Electronic Materials</i> , 2020, 6, 2000291.	5.1	11
16	Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal-Semiconductor Interface. <i>IEEE Transactions on Electron Devices</i> , 2020, , 1-4.	3.0	5
17	Electrode Engineering in MoS <sub>2</sub> MOSFET: Different Semiconductor/Metal Interfaces. <i>Advanced Electronic Materials</i> , 2022, 8, .	5.1	5
18	Comment on "Metal Semiconductor Field-Effect Transistor with MoS <sub>2</sub> /Conducting NiOx van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed". <i>ACS Nano</i> , 2016, 10, 1714-1715.	14.6	1

#	ARTICLE	IF	CITATIONS
19	MoS <sub>2</sub> Nanoribbon Transistor for Logic Electronics. IEEE Transactions on Electron Devices, 2022, 69, 3433-3438.	3.0	1